

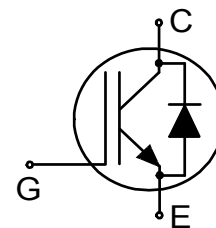
TRENCHSTOP™ RC-Series for hard switching applications

Cost effective monolithically integrated IGBT with Diode

Features:

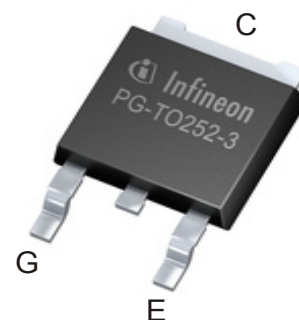
TRENCHSTOP™ Reverse Conducting (RC) technology for 600V applications offering

- Very tight parameter distribution
- Operating range up to 20kHz
- Maximum junction temperature 175°C
- Short circuit capability of 3μs
- Humidity robust design
- Pb-free lead plating; RoHS compliant
- Complete product spectrum and PSpice Models:
<http://www.infineon.com/rc-d2>



Potential Applications:

- Major Home Appliances
 - Air Conditioning
 - Refrigerators
- Drives
 - GPD (General Purpose Drives)



Product Validation:

Qualified for industrial applications according to the relevant tests of JEDEC47/20/22



Key Performance and Package Parameters

| Type | V _{CE} | I _C | V _{CEsat} , T _{vj} =25°C | T _{vjmax} | Marking | Package |
|-------------|-----------------|----------------|--|--------------------|---------|------------|
| IKD15N60RC2 | 600V | 15A | 2V | 175°C | K15DRC2 | PG-TO252-3 |

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Maximum Ratings

For optimum lifetime and reliability, Infineon recommends operating conditions that do not exceed 80% of the maximum ratings stated in this datasheet.

| Parameter | Symbol | Value | Unit |
|---|-------------|----------------------|--------------------|
| Collector-emitter voltage, $T_{vj} \geq 25^{\circ}\text{C}$ | V_{CE} | 600 | V |
| DC collector current, limited by T_{vjmax} $T_c = 25^{\circ}\text{C}$ $T_c = 100^{\circ}\text{C}$ | I_C | 28.0 18.6 | A |
| Pulsed collector current, t_p limited by T_{vjmax} | I_{Cpuls} | 45.0 | A |
| Turn off safe operating area $V_{CE} \leq 600\text{V}$, $T_{vj} \leq 175^{\circ}\text{C}$, $t_p = 1\mu\text{s}$ | - | 45.0 | A |
| Diode forward current, limited by T_{vjmax} $T_c = 25^{\circ}\text{C}$ $T_c = 100^{\circ}\text{C}$ | I_F | 12.5 6.6 | A |
| Diode pulsed current, t_p limited by T_{vjmax} | I_{Fpuls} | 45.0 | A |
| Gate-emitter voltage Transient Gate-emitter voltage ($t_p \leq 10\mu\text{s}$, $D < 0.010$) | V_{GE} | ± 20 ± 25 | V |
| Short circuit withstand time $V_{GE} = 15.0\text{V}$, $V_{CC} \leq 400\text{V}$ Allowed number of short circuits < 1000 Time between short circuits: $\geq 1.0\text{s}$ $T_{vj} = 150^{\circ}\text{C}$ | t_{SC} | 3 | μs |
| Power dissipation $T_c = 25^{\circ}\text{C}$ Power dissipation $T_c = 100^{\circ}\text{C}$ | P_{tot} | 115.4 57.7 | W |
| Operating junction temperature | T_{vj} | -40...+175 | $^{\circ}\text{C}$ |
| Storage temperature | T_{stg} | -55...+150 | $^{\circ}\text{C}$ |
| Soldering temperature, reflow soldering (MSL1 according to JEDEC J-STA-020) | | 260 | $^{\circ}\text{C}$ |

Thermal Resistance

| Parameter | Symbol | Conditions | Value | | | Unit |
|-----------|--------|------------|-------|------|------|------|
| | | | min. | typ. | max. | |

R_{th} Characteristics

| | | | | | | |
|---|---------------|--|---|---|------|-----|
| IGBT thermal resistance, ¹⁾ junction - case | $R_{th(j-c)}$ | | - | - | 1.30 | K/W |
| Diode thermal resistance, ²⁾ junction - case | $R_{th(j-c)}$ | | - | - | 5.00 | K/W |
| Thermal resistance, min. footprint junction - ambient | $R_{th(j-a)}$ | | - | - | 75 | K/W |
| Thermal resistance, 6cm ² Cu on PCB junction - ambient | $R_{th(j-a)}$ | | - | - | 50 | K/W |

¹⁾ R_{th}/Z_{th} based on single cooling pulse. Please be aware that a correct R_{th} measurement of the IGBT, is not possible using a thermocouple.

²⁾ R_{th}/Z_{th} based on single cooling pulse. Please be aware that a correct R_{th} measurement of the Diode, is not possible using a thermocouple.

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Electrical Characteristic, at $T_{vj} = 25^{\circ}\text{C}$, unless otherwise specified

| Parameter | Symbol | Conditions | Value | | | Unit |
|--------------------------------------|--------------|---|--------|--------------|------------|---------------|
| | | | min. | typ. | max. | |
| Static Characteristic | | | | | | |
| Collector-emitter saturation voltage | V_{CEsat} | $V_{GE} = 15.0\text{V}$, $I_C = 15.0\text{A}$ $T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 175^{\circ}\text{C}$ | - - | 2.00 2.40 | 2.30 - | V |
| Diode forward voltage | V_F | $V_{GE} = 0\text{V}$, $I_F = 15.0\text{A}$ $T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 175^{\circ}\text{C}$ | - - | 1.90 1.95 | 2.20 - | V |
| Gate-emitter threshold voltage | $V_{GE(th)}$ | $I_C = 0.16\text{mA}$, $V_{CE} = V_{GE}$ | 4.3 | 5.0 | 5.7 | V |
| Zero gate voltage collector current | I_{CES} | $V_{CE} = 600\text{V}$, $V_{GE} = 0\text{V}$ $T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 175^{\circ}\text{C}$ | - - | - - | 25 2500 | μA |
| Gate-emitter leakage current | I_{GES} | $V_{CE} = 0\text{V}$, $V_{GE} = 20\text{V}$ | - | - | 100 | nA |
| Transconductance | g_{fs} | $V_{CE} = 20\text{V}$, $I_C = 15.0\text{A}$ | - | 6.0 | - | S |
| Integrated gate resistor | r_G | | | none | | Ω |

Electrical Characteristic, at $T_{vj} = 25^{\circ}\text{C}$, unless otherwise specified

| Parameter | Symbol | Conditions | Value | | | Unit |
|-------------------------------|-----------|--|-------|------|------|---------------|
| | | | min. | typ. | max. | |
| Dynamic Characteristic | | | | | | |
| Input capacitance | C_{ies} | $V_{CE} = 25\text{V}$, $V_{GE} = 0\text{V}$ $f = 1000\text{kHz}$ | - | 575 | - | μF |
| Output capacitance | C_{oes} | | - | 28 | - | |
| Reverse transfer capacitance | C_{res} | | - | 21 | - | |
| Gate charge | Q_G | $V_{CC} = 480\text{V}$, $I_C = 15.0\text{A}$, $V_{GE} = 15\text{V}$ | - | 72.0 | - | nC |

Switching Characteristic, Inductive Load

| Parameter | Symbol | Conditions | Value | | | Unit |
|-----------|--------|------------|-------|------|------|------|
| | | | min. | typ. | max. | |

IGBT Characteristic, at $T_{vj} = 25^{\circ}\text{C}$

| | | | | | | |
|------------------------|--------------|--|---|------|---|----|
| Turn-on delay time | $t_{d(on)}$ | $T_{vj} = 25^{\circ}\text{C}$, $V_{CC} = 400\text{V}$, $I_C = 15.0\text{A}$, $V_{GE} = 0.0/15.0\text{V}$, $R_{G(on)} = 49.0\Omega$, $R_{G(off)} = 49.0\Omega$, $L\sigma = 30\text{nH}$, $C\sigma = 30\text{pF}$ $L\sigma$, $C\sigma$ from Fig. E Energy losses include "tail" and diode reverse recovery. | - | 18 | - | ns |
| Rise time | t_r | | - | 18 | - | ns |
| Turn-off delay time | $t_{d(off)}$ | | - | 374 | - | ns |
| Fall time | t_f | | - | 20 | - | ns |
| Turn-on energy | E_{on} | | - | 0.57 | - | mJ |
| Turn-off energy | E_{off} | | - | 0.35 | - | mJ |
| Total switching energy | E_{ts} | | - | 0.92 | - | mJ |

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Diode Characteristic, at $T_{vj} = 25^{\circ}\text{C}$

| | | | | | | |
|--|--------------|---|---|------|---|------------------------|
| Diode reverse recovery time | t_{rr} | $T_{vj} = 25^{\circ}\text{C}$, $V_R = 400\text{V}$, $I_F = 15.0\text{A}$, $di_F/dt = 787\text{A}/\mu\text{s}$ | - | 129 | - | ns |
| Diode reverse recovery charge | Q_{rr} | | - | 0.50 | - | μC |
| Diode peak reverse recovery current | I_{rrm} | | - | 11.2 | - | A |
| Diode peak rate of fall of reverse recovery current during t_b | di_{rr}/dt | | - | -93 | - | $\text{A}/\mu\text{s}$ |

Switching Characteristic, Inductive Load

| Parameter | Symbol | Conditions | Value | | | Unit |
|-----------|--------|------------|-------|------|------|------|
| | | | min. | typ. | max. | |

IGBT Characteristic, at $T_{vj} = 175^{\circ}\text{C}$

| | | | | | | |
|------------------------|--------------|--|---|------|---|----|
| Turn-on delay time | $t_{d(on)}$ | $T_{vj} = 175^{\circ}\text{C}$, $V_{CC} = 400\text{V}$, $I_C = 15.0\text{A}$, $V_{GE} = 0.0/15.0\text{V}$, $R_{G(on)} = 49.0\Omega$, $R_{G(off)} = 49.0\Omega$, $L\sigma = 30\text{nH}$, $C\sigma = 30\text{pF}$ $L\sigma$, $C\sigma$ from Fig. E Energy losses include "tail" and diode reverse recovery. | - | 16 | - | ns |
| Rise time | t_r | | - | 19 | - | ns |
| Turn-off delay time | $t_{d(off)}$ | | - | 393 | - | ns |
| Fall time | t_f | | - | 21 | - | ns |
| Turn-on energy | E_{on} | | - | 0.77 | - | mJ |
| Turn-off energy | E_{off} | | - | 0.39 | - | mJ |
| Total switching energy | E_{ts} | | - | 1.16 | - | mJ |

Diode Characteristic, at $T_{vj} = 175^{\circ}\text{C}$

| | | | | | | |
|--|--------------|--|---|------|---|------------------------|
| Diode reverse recovery time | t_{rr} | $T_{vj} = 175^{\circ}\text{C}$, $V_R = 400\text{V}$, $I_F = 15.0\text{A}$, $di_F/dt = 761\text{A}/\mu\text{s}$ | - | 199 | - | ns |
| Diode reverse recovery charge | Q_{rr} | | - | 1.04 | - | μC |
| Diode peak reverse recovery current | I_{rrm} | | - | 15.3 | - | A |
| Diode peak rate of fall of reverse recovery current during t_b | di_{rr}/dt | | - | -97 | - | $\text{A}/\mu\text{s}$ |

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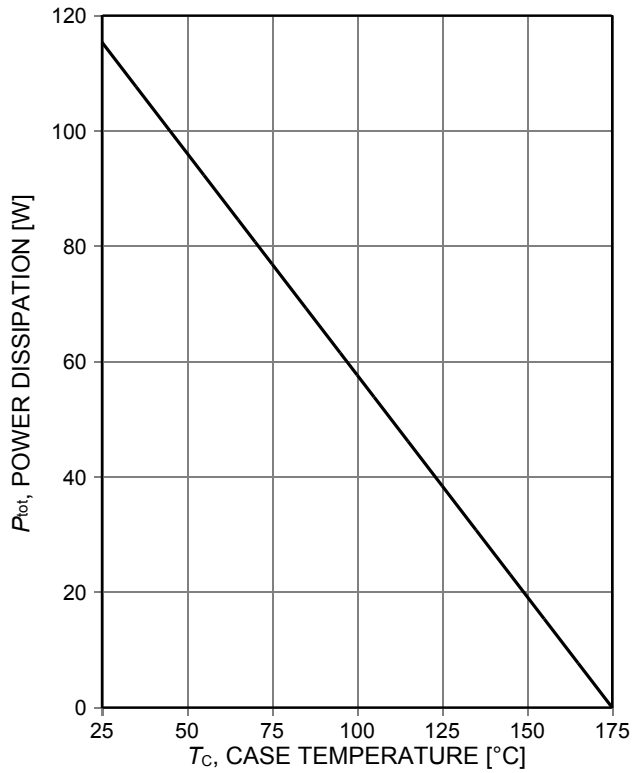


Figure 1. Power dissipation as a function of case temperature ($T_{vj} \leq 175^\circ\text{C}$)

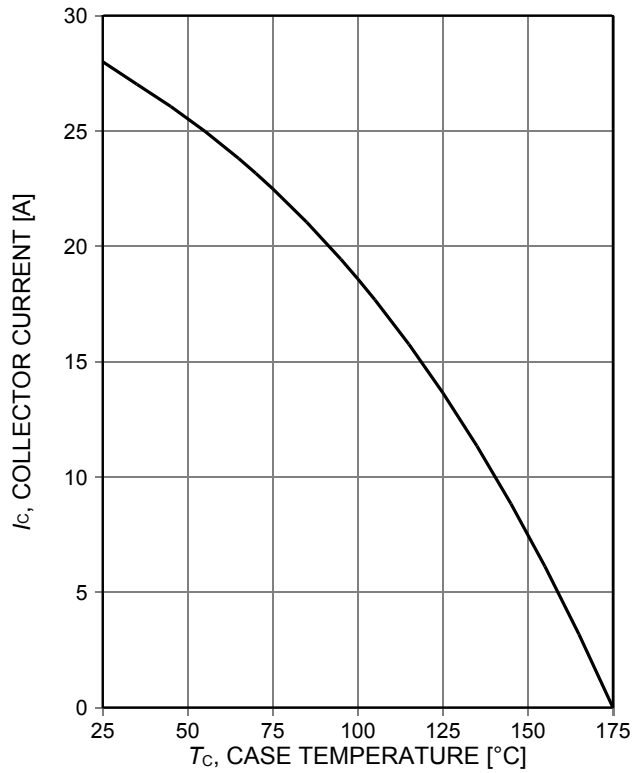


Figure 2. Collector current as a function of case temperature ($V_{GE} \geq 15\text{V}$, $T_{vj} \leq 175^\circ\text{C}$)

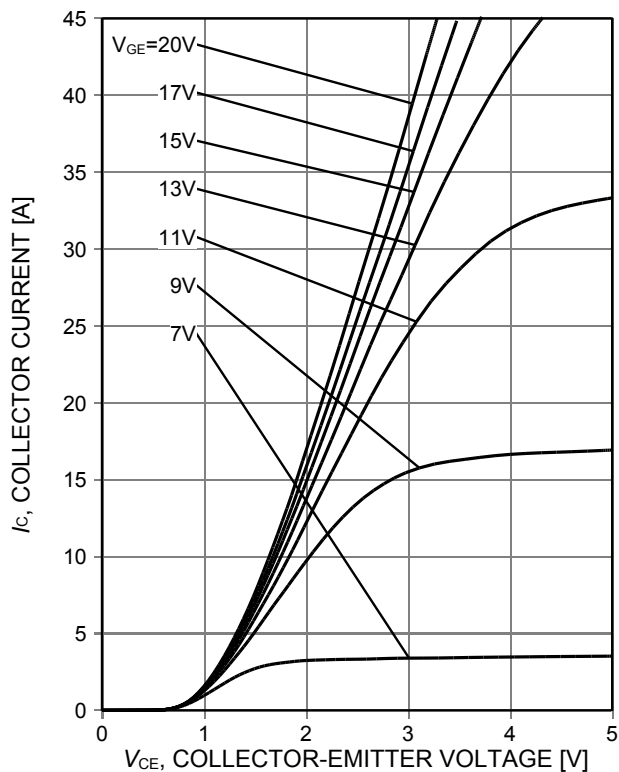


Figure 3. Typical output characteristic ($T_{vj} = 25^\circ\text{C}$)

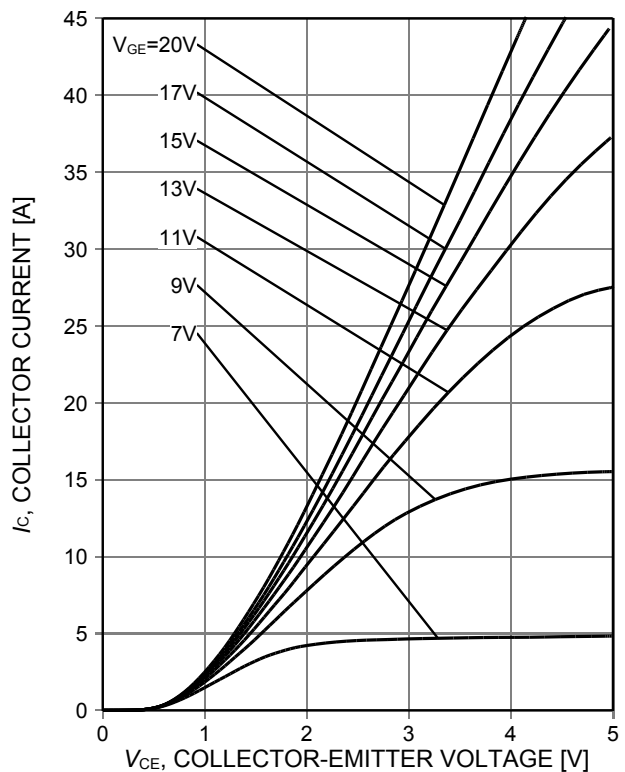


Figure 4. Typical output characteristic ($T_{vj} = 175^\circ\text{C}$)

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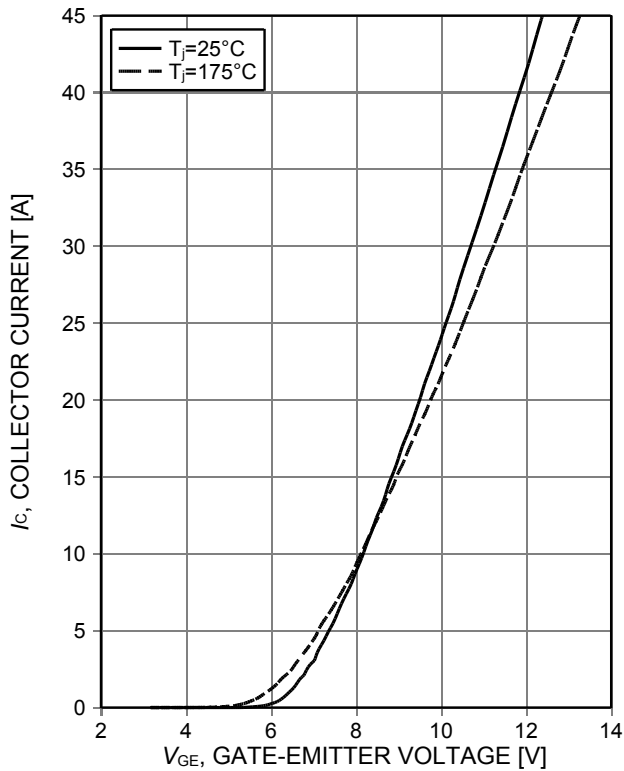


Figure 5. Typical transfer characteristic ($V_{CE}=20V$)

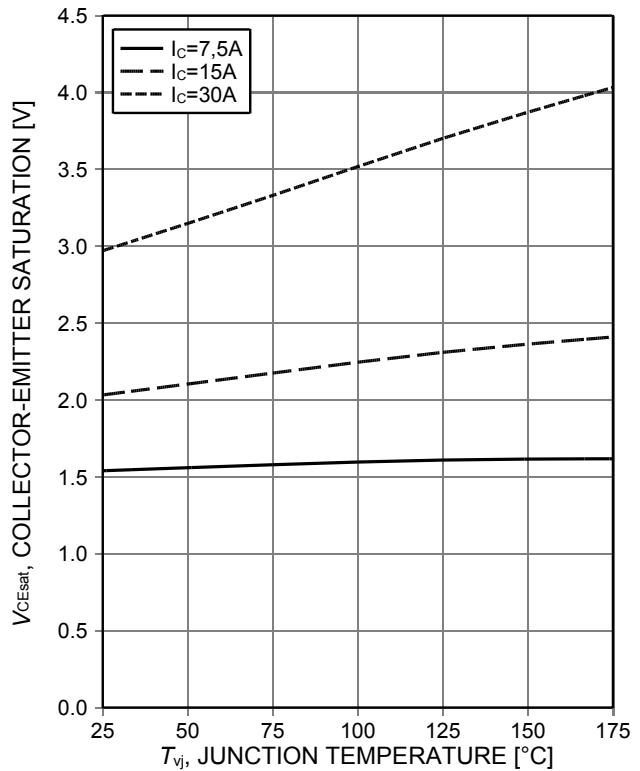


Figure 6. Typical collector-emitter saturation voltage as a function of junction temperature ($V_{GE}=15V$)

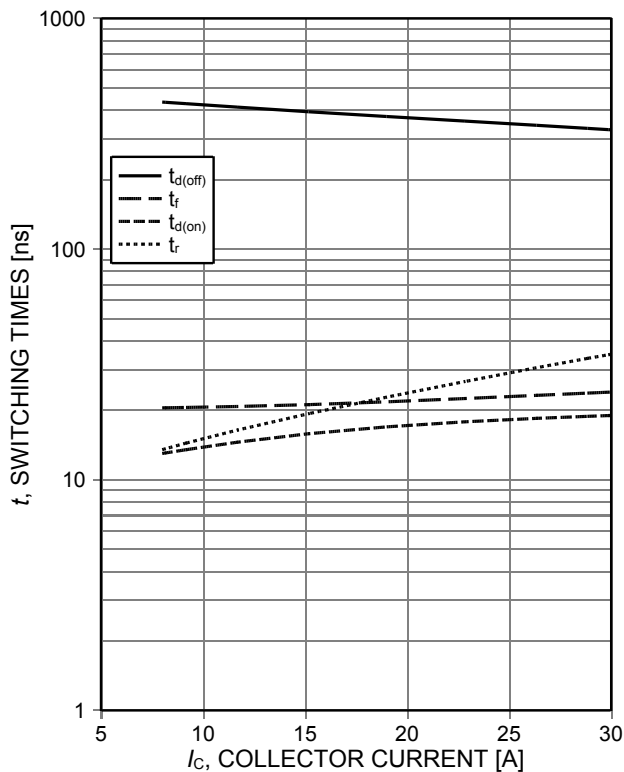


Figure 7. Typical switching times as a function of collector current (inductive load, $T_{vj}=175^{\circ}C$, $V_{CE}=400V$, $V_{GE}=15/0V$, $R_G=49\Omega$, Dynamic test circuit in Figure E)

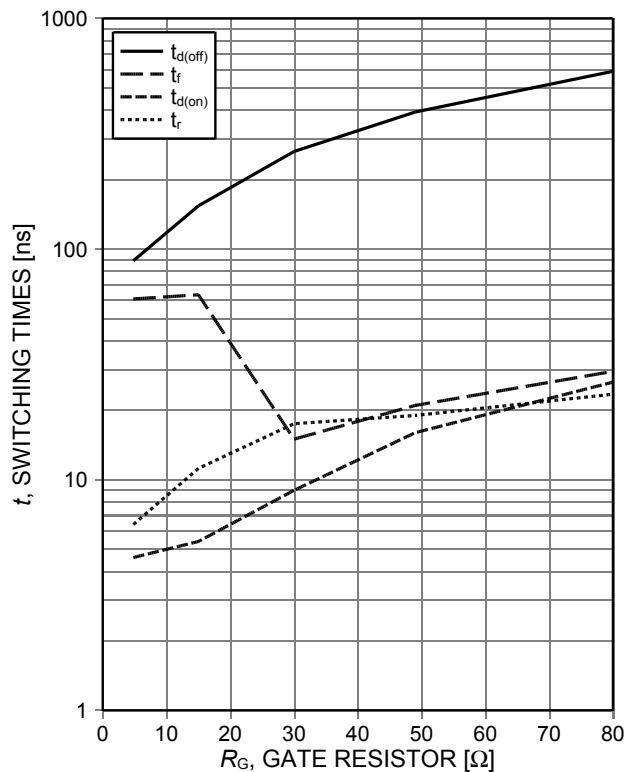


Figure 8. Typical switching times as a function of gate resistor (inductive load, $T_{vj}=175^{\circ}C$, $V_{CE}=400V$, $V_{GE}=15/0V$, $I_C=15A$, Dynamic test circuit in Figure E)

TRENCHSTOP™ RC-Series for hard switching applications

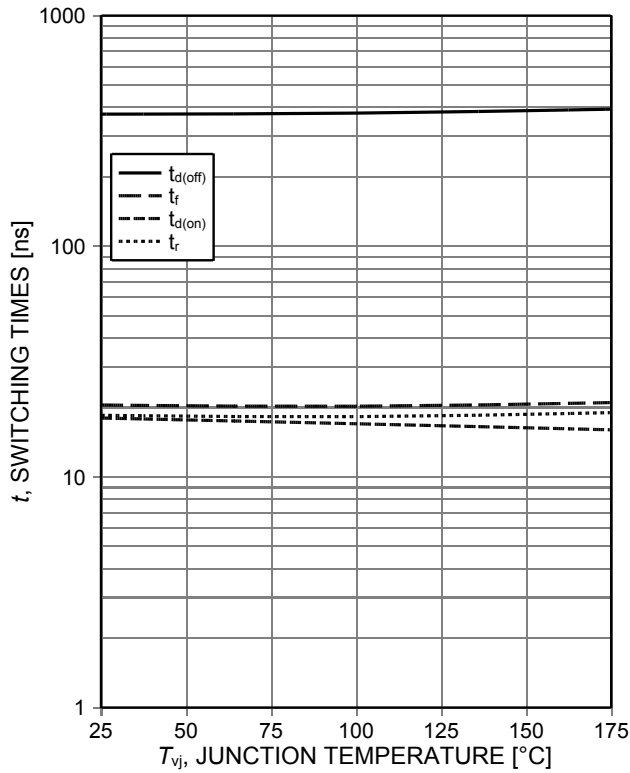


Figure 9. Typical switching times as a function of junction temperature (inductive load, $V_{CE}=400V$, $V_{GE}=15/0V$, $I_C=15A$, $R_G=49\Omega$, Dynamic test circuit in Figure E)

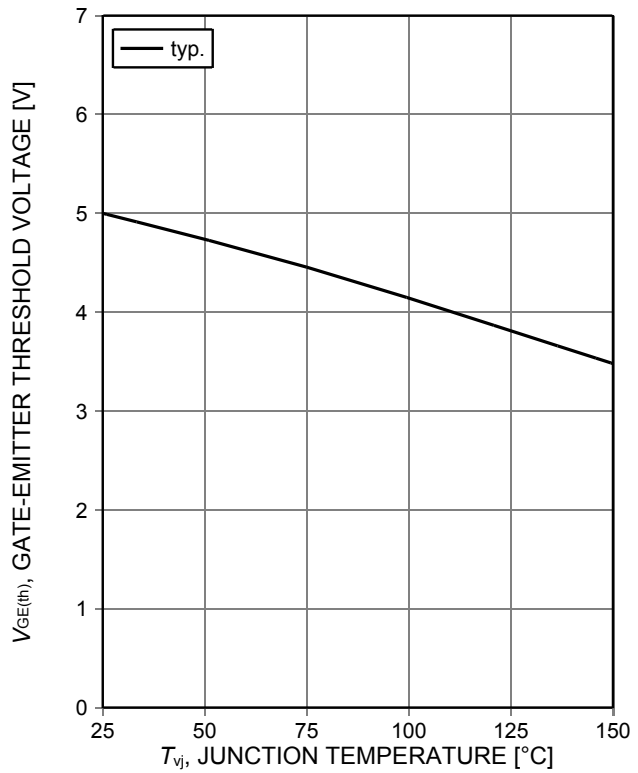


Figure 10. Gate-emitter threshold voltage as a function of junction temperature ($I_C=0.16mA$)

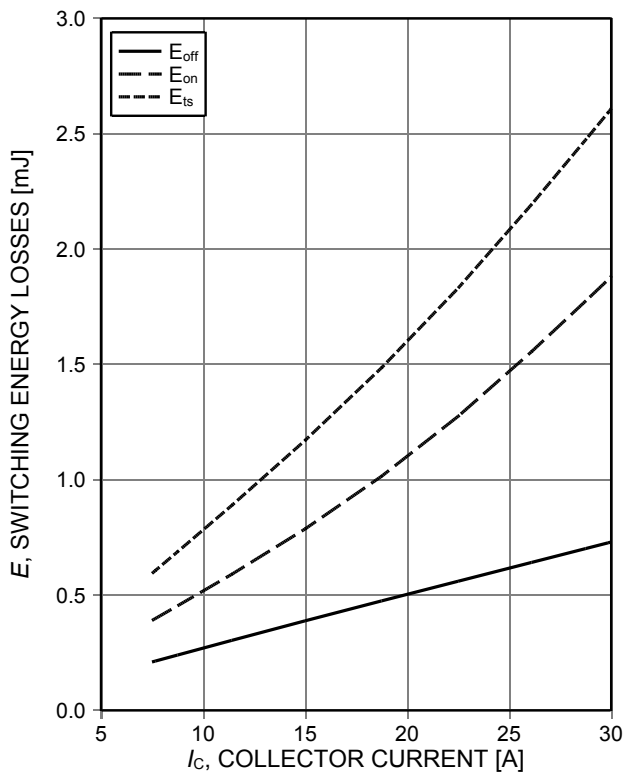


Figure 11. Typical switching energy losses as a function of collector current (inductive load, $T_{vj}=175^\circ C$, $V_{CE}=400V$, $V_{GE}=15/0V$, $R_G=49\Omega$, Dynamic test circuit in Figure E)

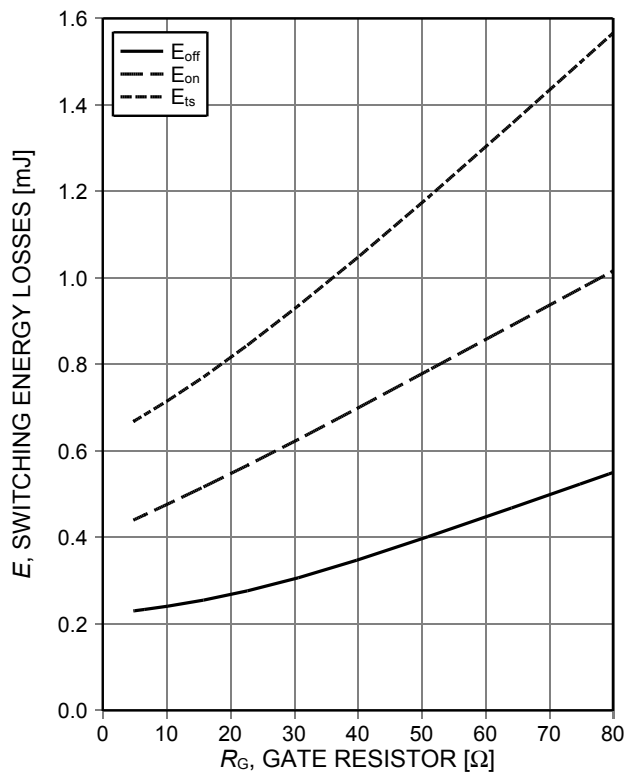


Figure 12. Typical switching energy losses as a function of gate resistor (inductive load, $T_{vj}=175^\circ C$, $V_{CE}=400V$, $V_{GE}=15/0V$, $I_C=15A$, Dynamic test circuit in Figure E)

TRENCHSTOP™ RC-Series for hard switching applications

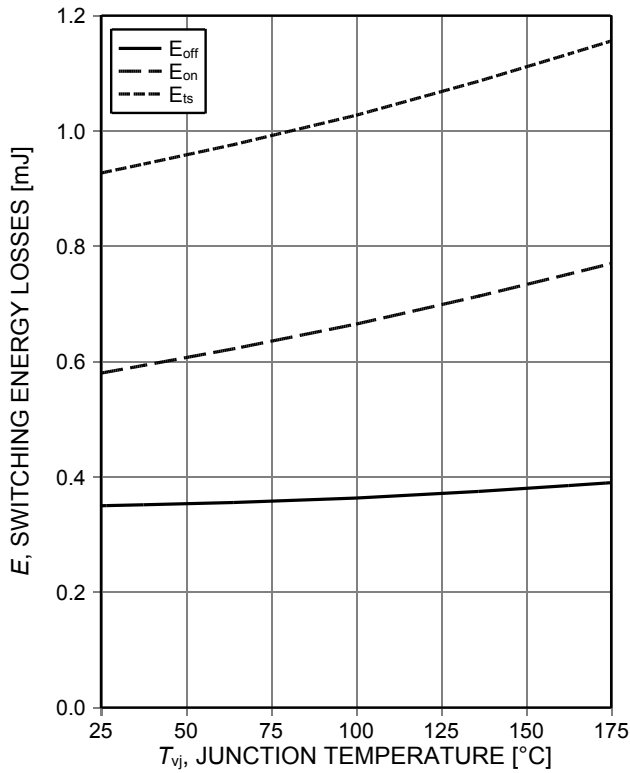


Figure 13. **Typical switching energy losses as a function of junction temperature** (inductive load, $V_{CE}=400V$, $V_{GE}=15/0V$, $I_C=15A$, $R_G=49\Omega$, Dynamic test circuit in Figure E)

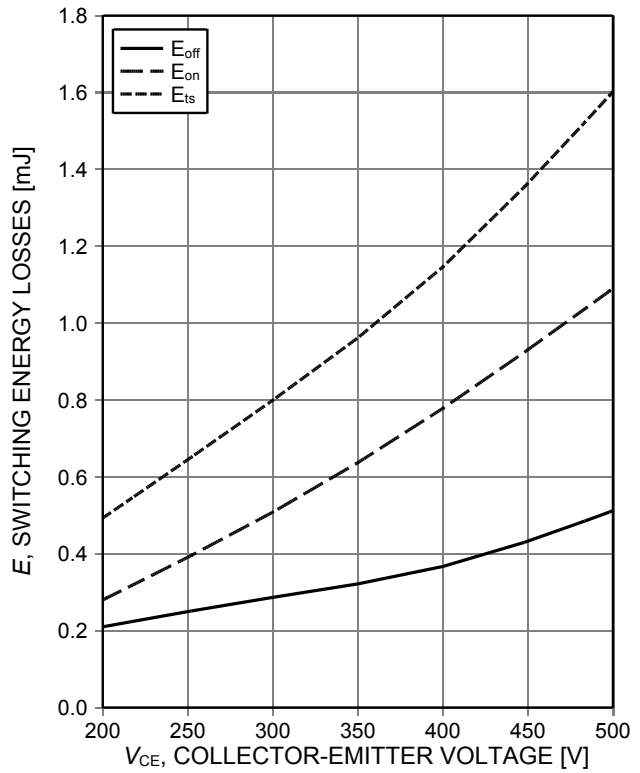


Figure 14. **Typical switching energy losses as a function of collector emitter voltage** (inductive load, $T_{vj}=175^\circ C$, $V_{GE}=15/0V$, $I_C=15A$, $R_G=49\Omega$, Dynamic test circuit in Figure E)

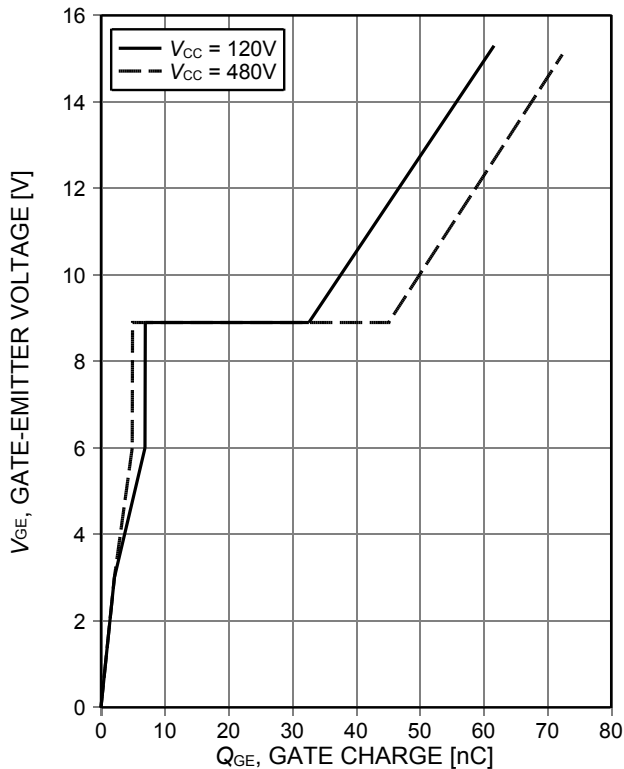


Figure 15. **Typical gate charge** ($I_C=15A$)

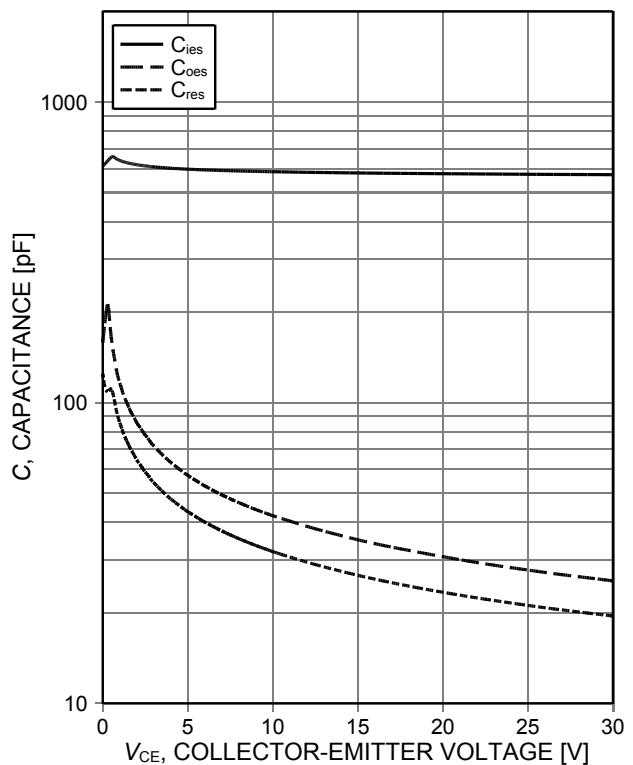


Figure 16. **Typical capacitance as a function of collector-emitter voltage** ($V_{GE}=0V$, $f=1MHz$)

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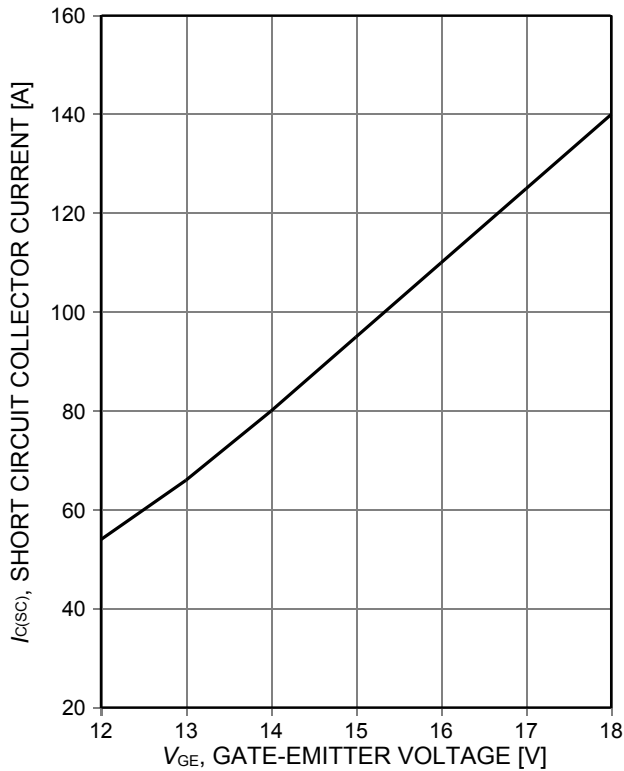


Figure 17. Typical short circuit collector current as a function of gate-emitter voltage ($V_{CE} \leq 400V$, $T_{vj} = 25^\circ C$)

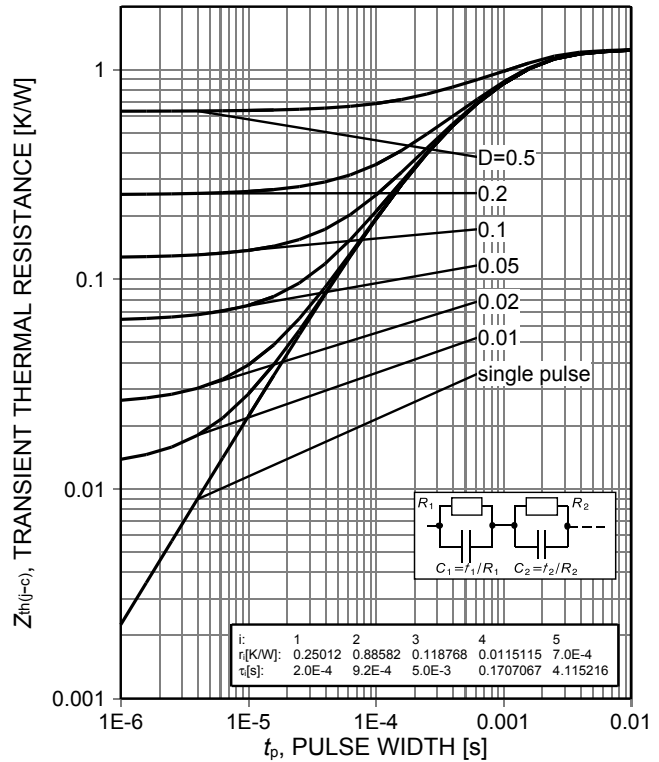


Figure 18. IGBT transient thermal resistance ($D = t_p / T$)

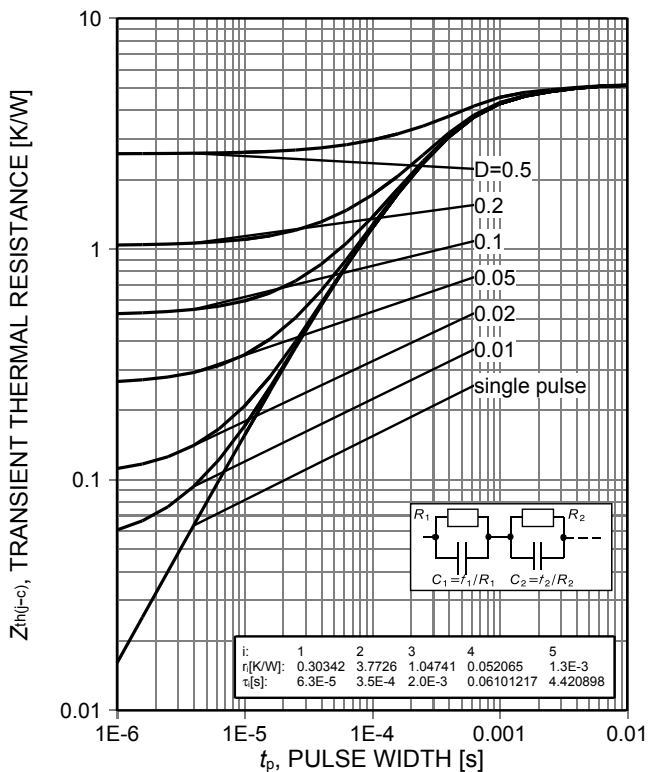


Figure 19. Diode transient thermal impedance as a function of pulse width ($D = t_p / T$)

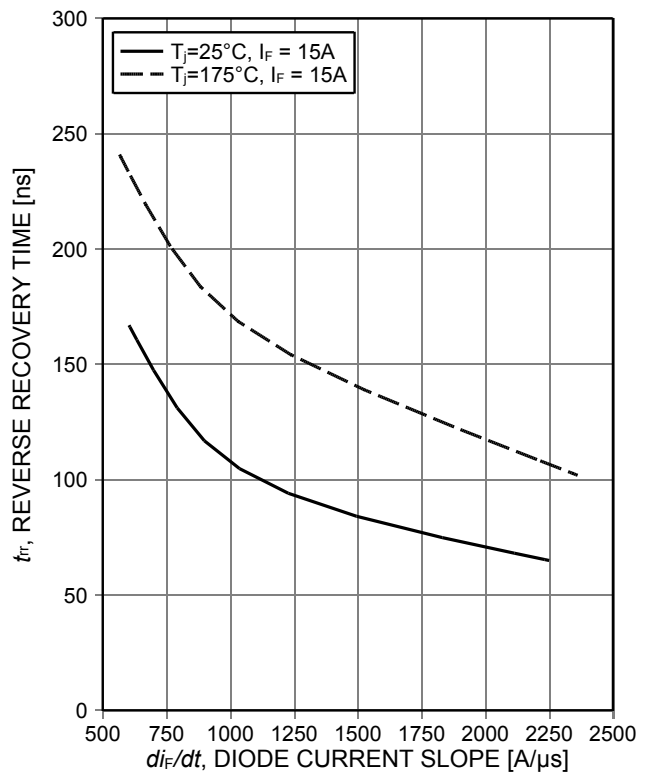


Figure 20. Typical reverse recovery time as a function of diode current slope ($V_R = 400V$)

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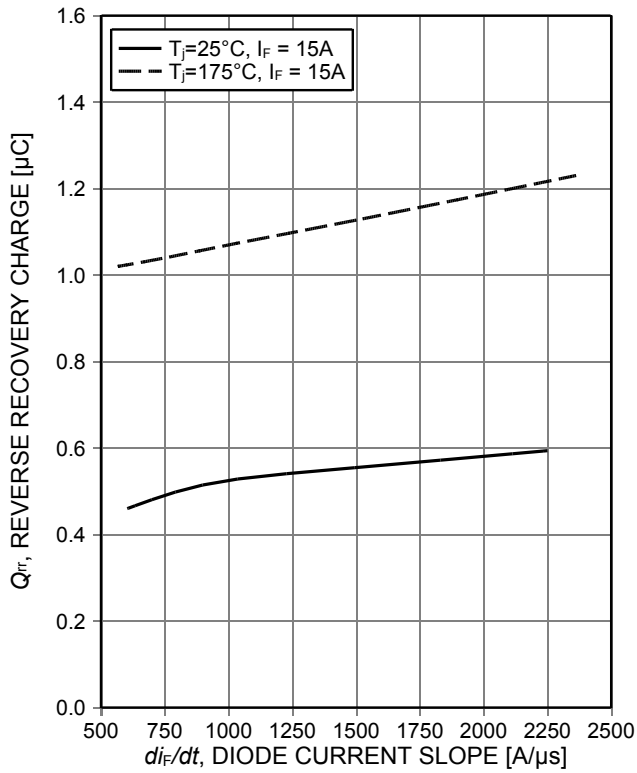


Figure 21. Typical reverse recovery charge as a function of diode current slope (VR=400V)

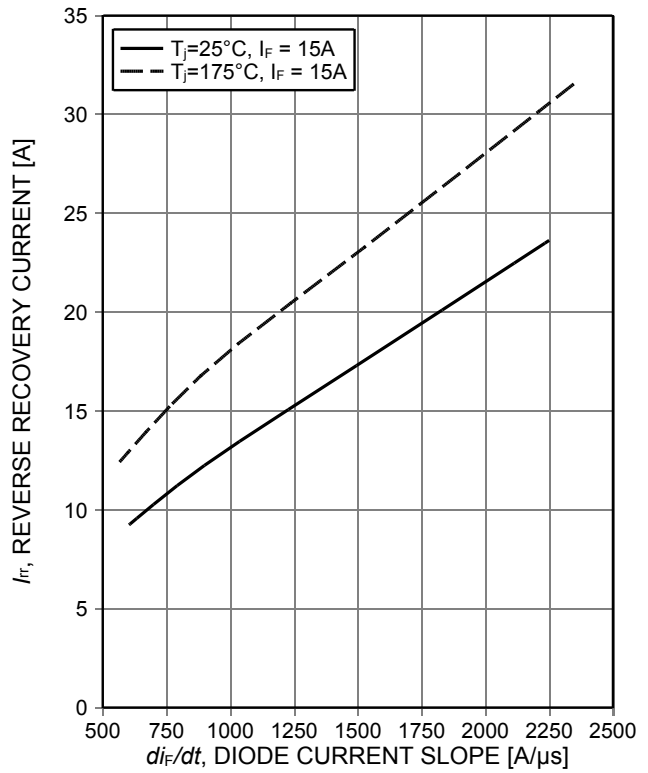


Figure 22. Typical reverse recovery current as a function of diode current slope (VR=400V)

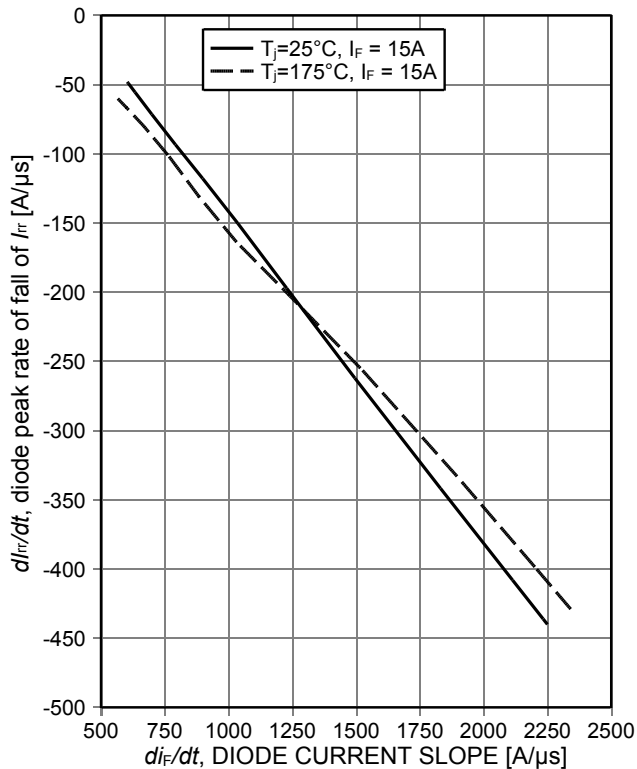


Figure 23. Typical diode peak rate of fall of reverse recovery current as a function of diode current slope (VR=400V)

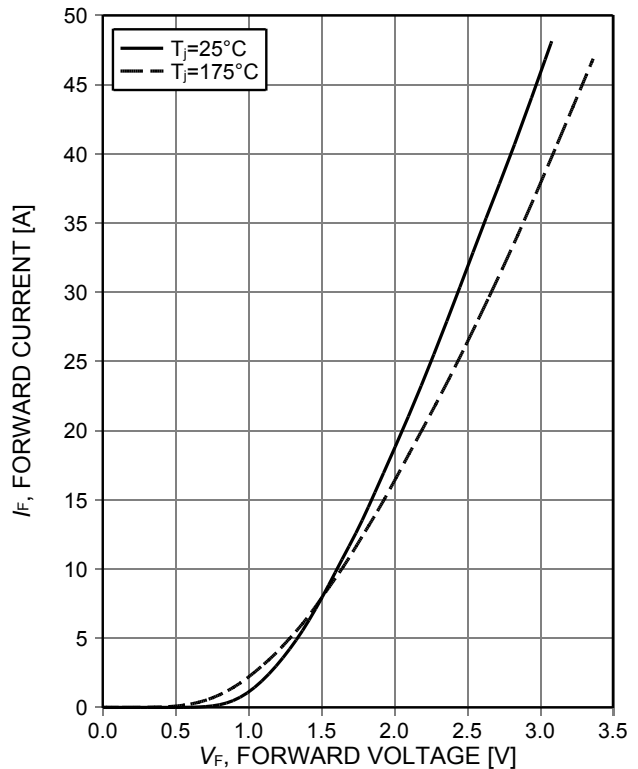


Figure 24. Typical diode forward current as a function of forward voltage

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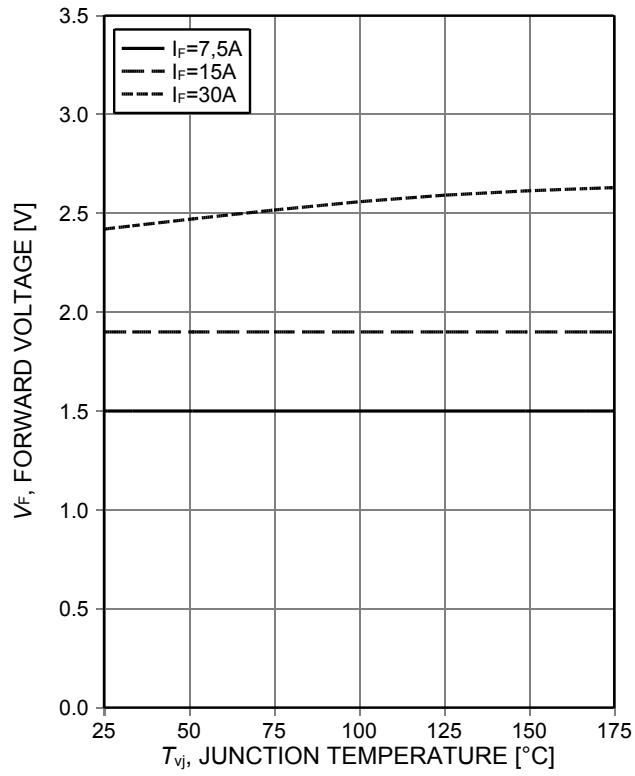
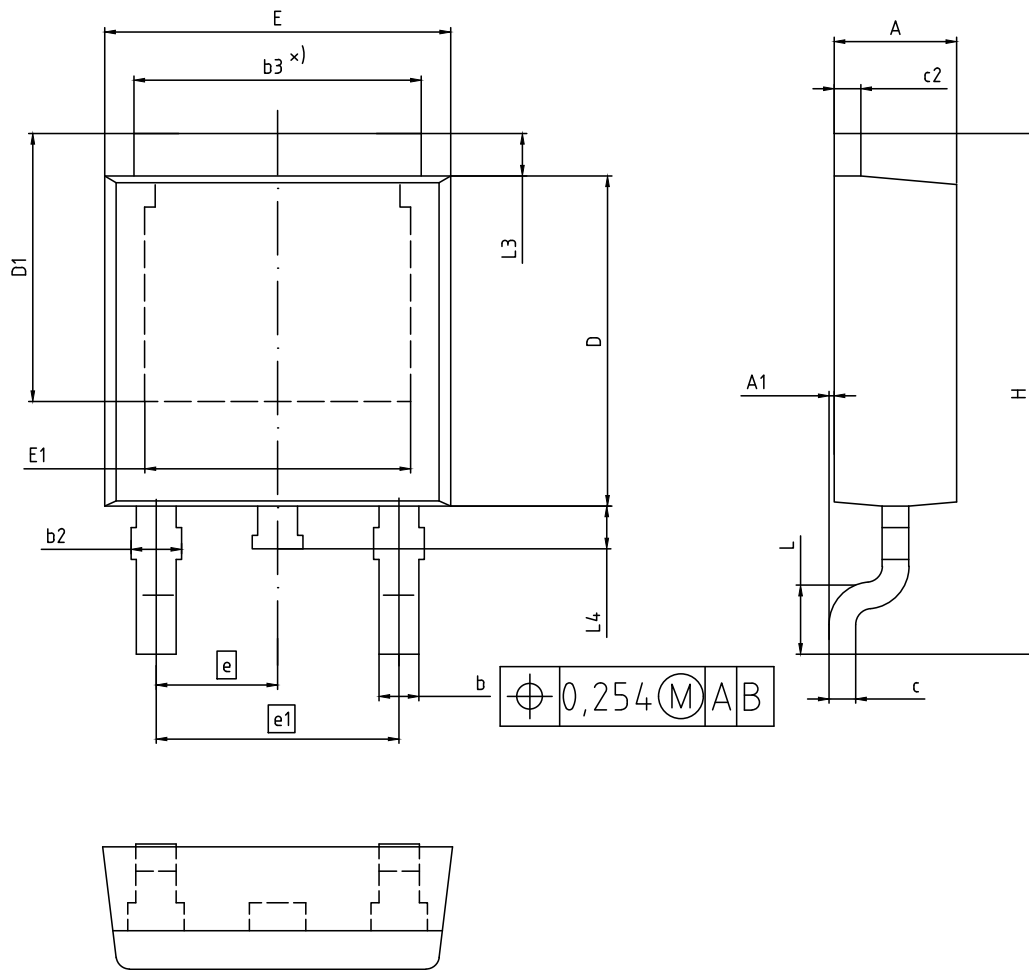


Figure 25. Typical diode forward voltage as a function of junction temperature

Package Drawing PG-TO252-3



NOTES:

1. ALL DIMENSIONS REFER TO JEDEC STANDARD TO-252 DO NOT INCLUDE MOLD FLASH OR PROTRUSIONS.

| DIM | MILLIMETERS | |
|-----|-------------|-------|
| | MIN | MAX |
| A | 2.16 | 2.41 |
| A1 | 0.00 | 0.15 |
| b | 0.64 | 0.89 |
| b2 | 0.65 | 1.15 |
| b3 | 4.95 | 5.50 |
| c | 0.46 | 0.61 |
| c2 | 0.40 | 0.98 |
| D | 5.97 | 6.22 |
| D1 | 5.02 | 5.84 |
| E | 6.35 | 6.73 |
| E1 | 4.32 | 5.21 |
| e | 2.29 (BSC) | |
| e1 | 4.57 (BSC) | |
| N | 3 | |
| H | 9.40 | 10.48 |
| L | 1.18 | 1.78 |
| L3 | 0.89 | 1.27 |
| L4 | 0.51 | 1.02 |

| |
|------------------------------------|
| DOCUMENT NO. Z8B00003328 |
| SCALE |
| EUROPEAN PROJECTION |
| ISSUE DATE 05-02-2016 |
| REVISION 06 |

Testing Conditions

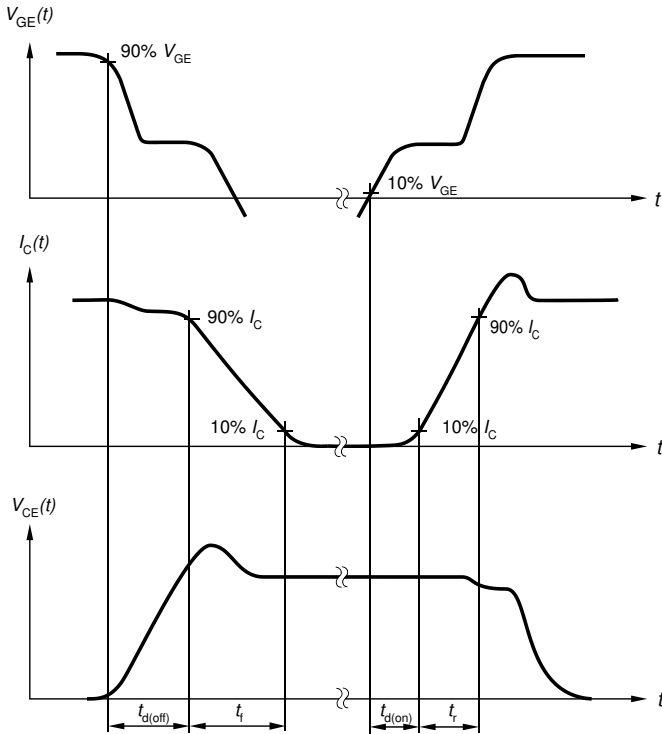


Figure A. Definition of switching times

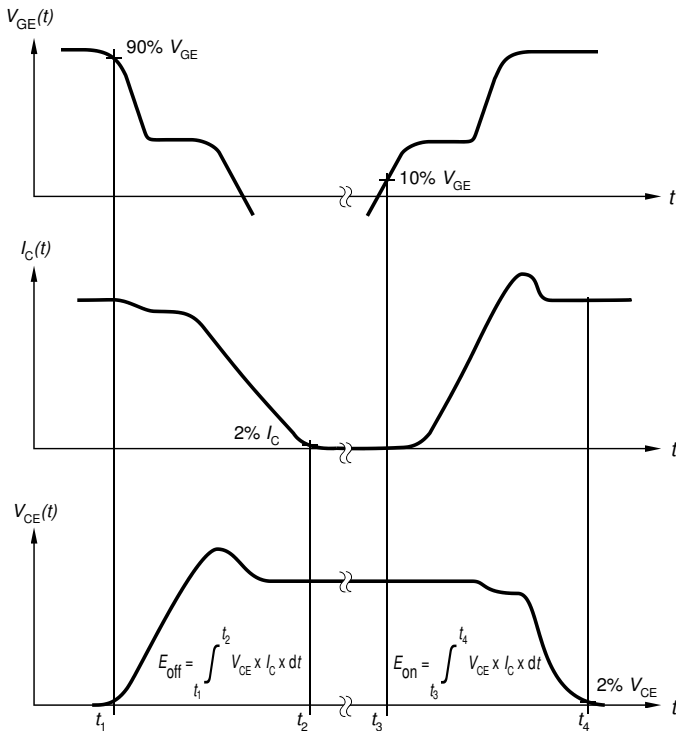


Figure B. Definition of switching losses

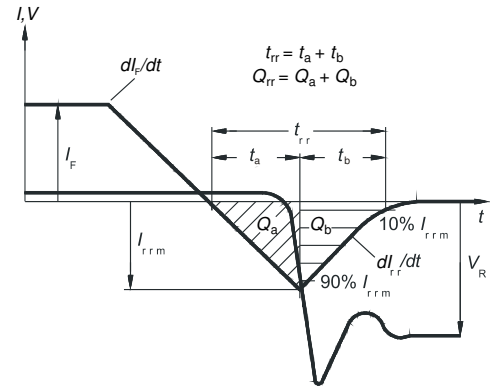


Figure C. Definition of diode switching characteristics

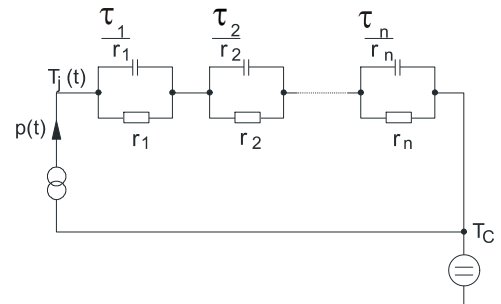


Figure D. Thermal equivalent circuit

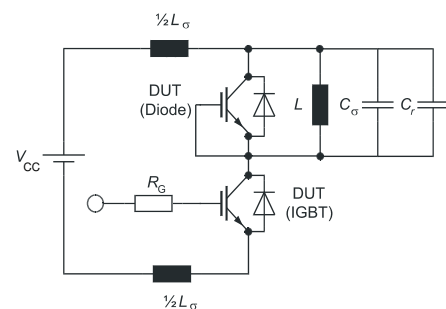


Figure E. Dynamic test circuit
Parasitic inductance L_{σ} ,
parasitic capacitor C_{σ} ,
relief capacitor C_r ,
(only for ZVT switching)

Revision History

IKD15N60RC2

Revision: 2020-09-28, Rev. 2.1

Previous Revision

| Revision | Date | Subjects (major changes since last revision) |
|----------|------------|--|
| 2.1 | 2020-09-28 | Final data sheet |

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